Miklos Csontos

List of Publications by Year
in descending order

18	380	932766 10	887659 17
papers	citations	h-index	g-index

18	18	18	566
all docs	docs citations	times ranked	citing authors

#	Article	IF	Citations
1	Noise Tailoring in Memristive Filaments. ACS Applied Materials & Interfaces, 2021, 13, 7453-7460.	4.0	16
2	Noise diagnostics of graphene interconnects for atomic-scale electronics. Npj 2D Materials and Applications, 2021, 5, .	3.9	7
3	A non-oxidizing fabrication method for lithographic break junctions of sensitive metals. Nanoscale Advances, 2020, 2, 3829-3833.	2.2	0
4	Breaking the Quantum PIN Code of Atomic Synapses. Nano Letters, 2020, 20, 1192-1200.	4.5	7
5	Nanosecond resistive switching in Ag/AgI/PtIr nanojunctions. Beilstein Journal of Nanotechnology, 2020, 11, 92-100.	1.5	7
6	Universal 1/f type current noise of Ag filaments in redox-based memristive nanojunctions. Nanoscale, 2019, 11, 4719-4725.	2.8	19
7	In situ impedance matching in Nb/Nb₂O₅/PtIr memristive nanojunctions for ultra-fast neuromorphic operation. Nanoscale, 2018, 10, 19290-19296.	2.8	6
8	Multiple Physical Time Scales and Dead Time Rule in Few-Nanometers Sized Grapheneâ€“SiO_x-Graphene Memristors. Nano Letters, 2017, 17, 6783-6789.	4.5	20
9	Asymmetry-induced resistive switching in Ag-Ag2S-Ag memristors enabling a simplified atomic-scale memory design. Scientific Reports, 2016, 6, 30775.	1.6	30
10	Resistive switching in metallic Ag₂S memristors due to a local overheating induced phase transition. Nanoscale, 2015, 7, 11248-11254.	2.8	19
11	Non-exponential resistive switching in Ag₂S memristors: a key to nanometer-scale non-volatile memory devices. Nanoscale, 2015, 7, 4394-4399.	2.8	32
12	A fast operation of nanometer-scale metallic memristors: highly transparent conductance channels in Ag₂S devices. Nanoscale, 2014, 6, 2613-2617.	2.8	23
13	Improved thermal relaxation method for the simultaneous measurement of the specific heat and thermal conductivity. European Physical Journal B, 2010, 74, 27-33.	0.6	7
14	Anomalous Hall Effect in the (In,Mn)Sb Dilute Magnetic Semiconductor. Physical Review Letters, 2008, 100, 107201.	2.9	38
15	Pressure-induced ferromagnetism in (In,Mn)Sb dilute magnetic semiconductor. Nature Materials, 2005, 4, 447-449.	13.3	82
16	Magnetic Scattering of Spin Polarized Carriers in(In,Mn)SbDilute Magnetic Semiconductor. Physical Review Letters, 2005, 95, 227203.	2.9	49
17	Effect of hydrostatic pressure on the transport properties in magnetic semiconductors. Physica Status Solidi C: Current Topics in Solid State Physics, 2004, 1, 3571-3574.	0.8	11
18	Enhanced granular magnetoresistance due to ferromagnetic layers. Solid State Communications, 2003, 126, 427-429.	0.9	7